

UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

~~MICRON TECHNOLOGY, INC., INTEL CORPORATION,
AND GLOBALFOUNDRIES U.S., INC.~~
~~Petitioners~~

~~SAMSUNG ELECTRONICS COMPANY, LTD.~~
~~Petitioner~~

v.

DANIEL L. FLAMM
Patent Owner

~~Case IPR No. **Unassigned**~~

~~U.S. Patent No. 5,711,849
Title: **PROCESS OPTIMIZATION IN GAS PHASE DRY ETCHING**~~

~~**Petition for *Inter Partes* Review of U.S. Patent No. 5,711,849 Under
35 U.S.C. §§ 311-319 and 37 C.F.R. §§ 42.1-.80, 42.100-
.123**~~

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1.	INTRODUCTION	1
2.	REQUIREMENTS FOR PETITION FOR <i>INTER PARTES</i> REVIEW	1
	2.1. Grounds for Standing (37 C.F.R. § 42.104(a))	1
	2.2. Notice of Lead and Backup Counsel and Service Information	1
	2.3. Notice of Real Parties in Interest (37 C.F.R. § 42.8(b)(1))	3
	2.4. Notice of Related Matters (37 C.F.R. § 42.8(b)(2))	3
	2.5. Fee for <i>Inter Partes</i> Review	4
	2.6. Proof of Service	4
3.	IDENTIFICATION OF CLAIMS BEING CHALLENGED (§ 42.104(B))	4
4.	OVERVIEW OF THE 849 <u>U.S. PATENT</u> <u>5 NO. 5,711,849</u>	
5.	849 PATENT PROSECUTION HISTORY	11
6.	CLAIM CONSTRUCTION	12
	6.1. Applicable Law	12
	6.2. Construction of Claim Terms	13
	6.2.1. “surface reaction rate constant” (all claims)	13
7.	PERSON HAVING ORDINARY SKILL IN THE ART	15
8.	DESCRIPTION OF THE PRIOR ART	16
	8.1. Alkire (Ex. 1005)	16
	8.2. Kao (Ex. 1006)	19
	8.3. Flamm (Ex. 1007)	23
	8.4. Motivations To Combine: Alkire in Combination with Kao	24
	8.5. Motivations To Combine: Alkire in Combination with Kao and Flamm	25
9.	GROUND #1: CLAIMS 1-29 OF THE 849 PATENT ARE UNPATENTABLE AS OBVIOUS OVER ALKIRE IN VIEW OF KAO	26
	9.1. Claim 1 is obvious over Alkire in view of Kao	27
	9.1.1. [1.P] “A device fabrication method comprising the steps of:”	27

9.1.2. [1.1] “providing a plasma etching apparatus comprising a substrate therein, said substrate comprising a top surface and a film overlying said top surface, said film comprising a top film surface;”	28
9.1.3. [1.2] “etching said top film surface to define a relatively non-uniform etching profile on said film, and defining etch rate data comprising an etch rate and a spatial coordinate which defines a position within said relatively non-uniform etching profile on said substrate, said etching comprising a reaction between a gas phase etchant and said film; and”	29
9.1.4. [1.3] “extracting a surface reaction rate constant from said etch rate data, and using said surface reaction rate constant in the fabrication of a device.”	32
9.2. Claim 10 is obvious over Alkire in view of Kao	37
9.2.1. [10.P] “A method of designing a reactor comprising the steps of:”	37
9.2.2. [10.1] “providing a first plasma etching apparatus comprising a substrate therein, said substrate comprising a top surface and a film overlying said top surface, said film comprising a top film surface”	37
9.2.3. [10.2] “etching said top film surface to define a relatively non-uniform etching profile on said film, and defining etch rate data comprising an etch rate and a spatial coordinate which defines a position within said relatively non-uniform etching profile on said film of said substrate, said etching comprising a reaction between a gas phase etchant and said film; and”	37
9.2.4. [10.3] “extracting a surface reaction rate constant from said etch rate data, and using said surface reaction rate constant in designing a second plasma etching apparatus.”	38
9.3. Claim 20 is obvious over Alkire in view of Kao	39
9.3.1. [20.p] “A substrate fabrication method, using a plasma etching apparatus, said method comprising:”	39

9.3.2.	[20.1] “providing a substrate selected from a group consisting of a semiconductor wafer, a plate, and a flat panel display, said substrate comprising a top surface;”	39
9.3.3.	[20.2] “forming a film overlying said top surface, said film comprising a top film surface;”	40
9.3.4.	[20.3] “etching said top film surface to define a relatively non-uniform profile on said film, and defining etch rate data comprising an etch rate and a spatial coordinate which defines a position within said relatively non-uniform etching profile of said film on said substrate, said etching comprising a reaction between a gas phase etchant and said film; and”	40
9.3.5.	[20.4] “extracting a surface reaction rate constant from said etch rate data, and using said surface reaction rate constant.”	40
9.4.	Claim 22 is obvious over Alkire in view of Kao	40
9.4.1.	[22.P] “A method of fabricating an integrated circuit device, using a plasma etching apparatus, said method comprising:”	40
9.4.2.	[22.1] “providing a uniformity value and a surface reaction rate constant for an etching reaction, said etching reaction including a substrate and etchant species;”	41
9.4.3.	[22.2] “defining etching parameters providing said uniformity value; and”	42
9.4.4.	[22.3] “adjusting at least one of said etching parameters using said surface reaction rate constant to produce a selected etching rate”	44
9.4.5.	[22.4] “wherein said etching rate providing an etching condition for fabrication of an integrated circuit device.”	46
9.5.	Claim 26 is obvious over Alkire in view of Kao	46
9.5.1.	[26.P] “A process for fabricating a device using a plasma etching apparatus, said device being fabricated by use of a surface reaction rate constant, said surface	

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